



HiPerFET™ Power MOSFETs Q-Class

N-Channel Enhancement Mode
Avalanche Rated, Low Q_g , High dv/dt

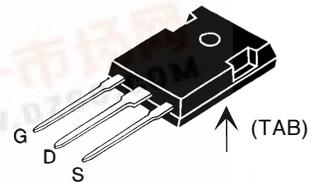
	V_{DSS}	I_{D25}	$R_{DS(on)}$
IXFH/IXFT 24N50Q	500 V	24 A	0.23 Ω
IXFH/IXFT 26N50Q	500 V	26 A	0.20 Ω

$t_{rr} \leq 250$ ns



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ M Ω	500	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	24N50	24 A
		26N50	26 A
I_{DM}	$T_C = 25^\circ\text{C}$, Note 1	24N50	96 A
		26N50	104 A
I_{AR}	$T_C = 25^\circ\text{C}$	24N50	24 A
		26N50	26 A
E_{AR}	$T_C = 25^\circ\text{C}$	30	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100$ A/ μs , $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-247 AD (IXFH)



TO-268 (D3) (IXFT) Case Style



G = Gate, D = Drain, S = Source, TAB = Drain

Features

- IXYS advanced low Q_g process
- International standard packages
- Low $R_{DS(on)}$
- Unclamped Inductive Switching (UIS) rated
- Fast switching
- Molding epoxies meet UL 94 V-0 flammability classification

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 250$ μA	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4$ mA	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20$ V _{DC} , $V_{DS} = 0$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0$ V	$T_J = 25^\circ\text{C}$		25 μA
		$T_J = 125^\circ\text{C}$		1 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 0.5 I_{D25}$ Note 2	24N50Q		0.23 Ω
		26N50Q		0.20 Ω

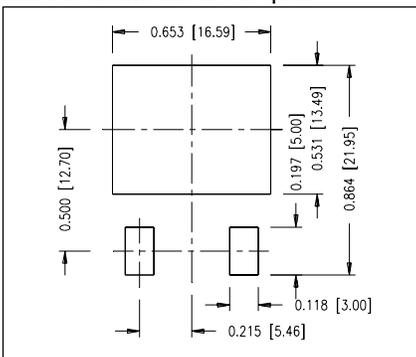


Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	V _{DS} = 10 V; I _D = 0.5 I _{D25} , Note 2	14	24	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz	3900		pF
C_{oss}		500		pF
C_{rss}		130		pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25} R _G = 2 Ω (External),	28		ns
t_r		30		ns
t_{d(off)}		55		ns
t_f		16		ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}	95		nC
Q_{gs}		27		nC
Q_{gd}		40		nC
R_{thJC}	(TO-247)	0.42		K/W
R_{thCK}		0.25		K/W

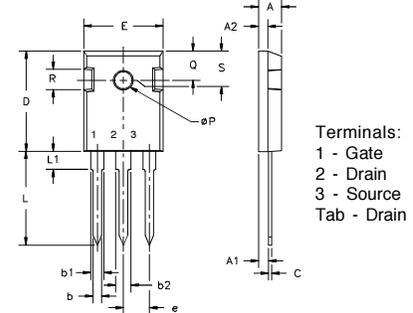
Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
I_S	V _{GS} = 0 V	24N50Q 26N50Q		24 26 A
I_{SM}	Repetitive; Note 1	24N50Q 26N50Q		96 104 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.3 V
t_{rr}	I _F = I _S , -di/dt = 100 A/μs, V _R = 100 V	0.85		250 ns
Q_{RM}		8		μC
I_{RM}				A

Note 1. Pulse width limited by T_{JM}
 2. Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %

Min Recommended Footprint



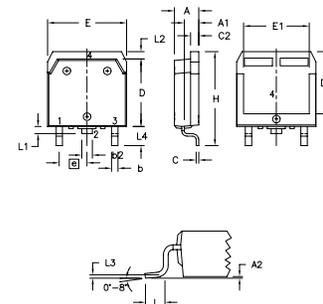
TO-247 AD Outline



Terminals:
 1 - Gate
 2 - Drain
 3 - Source
 Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

TO-268 Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3		0.25	BSC	.010
L4	3.80	4.10	.150	.161

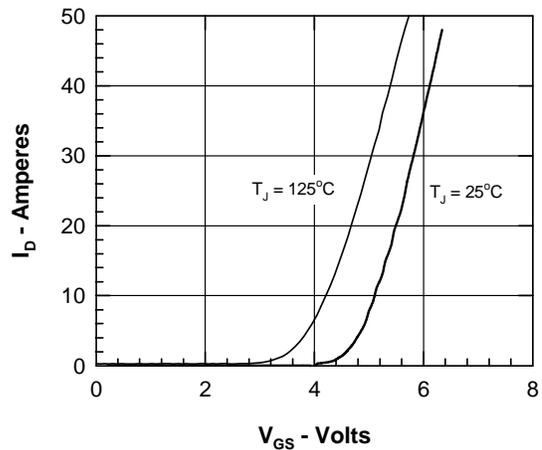
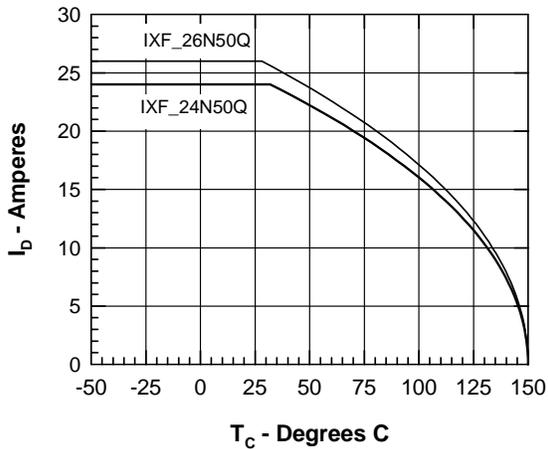
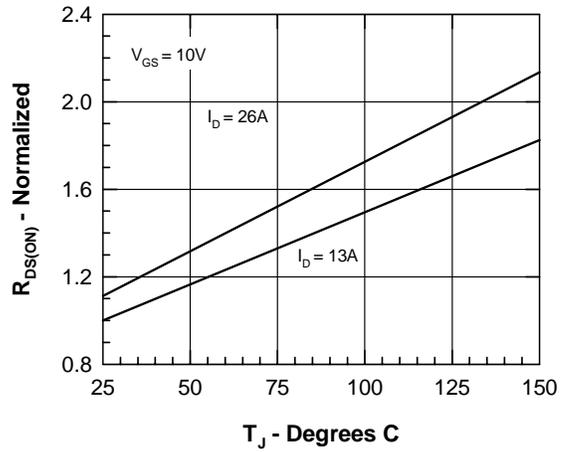
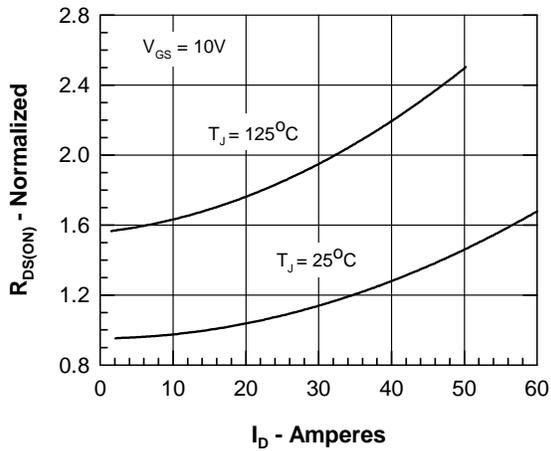
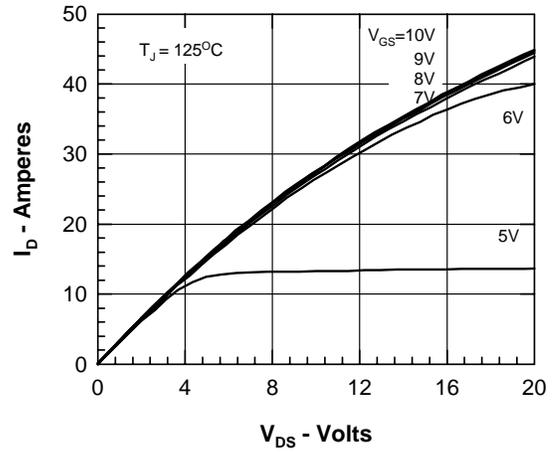
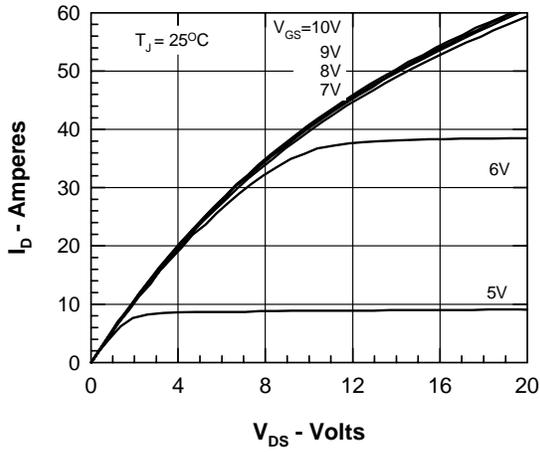


Fig.5 Drain Current vs. Case Temperature

Fig.6 Drain Current vs Gate Source Voltage

C

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